

Citations for Ion : **Cd**

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1966	VanLint, V. A. J. Wyatt, M. E. Schmitt, R. A. Suffredini, C. S. Nichols, D. K. 'Range of Photoparticle Recoil Atoms on Solids' <i>Phys. Rev.</i> , 147 , 242-48 (1966) <i>Comment</i> : R. (.001- 5 epsilon) Ti, Sc, Cr, Fe, Mn, Ni, Co, Ge, Zr, Y, Sr, Mo, Rh, Pd, Ag, Cd, Sn, Gd, Ta, Au, Th -> Al, Cu	1966-VanL
1969	Bottiger, J. Bason, F. 'Energy Loss of Heavy Ions Along Low-Index Directions in Gold Single Crystals' <i>Rad. Effects</i> , 2 , 105-10 (1969) <i>Comment</i> : S. (300-970 keV) N, Ne, Na, Mg, S, Cl, Ar, K, Si, Mn, Fe, Kr, Y, Mo, Ag, Cd, Sb, Xe -> Au	1969-Bott
1973	Chu, W. K. Crowder, B. L. Mayer, J. W. Ziegler, J. F. 'Range Distributions of Implanted Ions in SiO ₂ , Si ₃ N ₄ , and Al ₂ O ₃ ' <i>Appl. Phys. Letters</i> , 22 , 490-92 (1973) <i>Comment</i> : R, dR. Zn, Ga, As, Se, Cd, Te (140-300 keV) -> SiO ₂ , Si ₃ N ₄ , Al ₂ O ₃	1973-Chu
1973	Chu, W. K. Crowder, B. L. Mayer, J. W. Ziegler, J. F. 'Ranges and Distributions of Ions Implanted into Dielectrics' <i>B.L. Crowder (Ed.): Ion Implantation in Semiconductors and Other Materials. Plenum. N. Y. 225-41 (1973)</i> <i>Comment</i> : R.dR. (140-300 keV) Zn, Ga, As, Se, Cd, Te, Zn -> Si, Si ₃ N ₄ , Al ₂ O ₃	1973-Chu 2
1974	Grant, W. A. Williams, J. S. Dodds, D. 'Measurement of Projected and Lateral Range Parameters for Low Energy Heavy Ions in Silicon by Rutherford Backscattering' <i>Meyer, G. Linker and F. Kappeler (Ed.): Ion Beam Surface Layer Analysis, Plenum, N. Y., P. 235-44 (1974)</i> <i>Comment</i> : R, dR, dR(Lateral). 10-80 keV Pb, 50-400 keV Bi, 40 keV Ar, Cu, Kr, Cd, Al, Dy, W -> Si	1974-Gran
1974	Lemberg, I. Kh. Pasternak, A. A. 'New Method of Investigating the Electronic and Ion-Atomic Mechanisms of Stopping Heavy Ions in Matter' <i>Zh. Etf Pis. Red.</i> , 19 , 784-87 (1974). [<i>Engl. Trans. JETP Letters</i> , 19 , 401-02 (1974).] <i>Comment</i> : S. 18 MeV Cd -> Cd, 12.5 MeV Ni -> Ni	1974-Lemb
1976	Benmalek, M. Thomas, J. P. Mackowski, J. M. 'Ion-Bombardment of Amorphous Semiconductors and Related Evolution of Structural and Electrical Properties' <i>Ion Implantation in Semiconductors, Ed. by F. Chernow, J. A. Borders, D. K. Brice, 637-647 (1976)</i> <i>Comment</i> : R. 20-300 keV Ne, Ar, Ge, Cd, Te, Xe, Au -> Ge	1976-Benm
1976	Grant, W. A. Williams, J. S. Dodds, D. 'Measurement of the Lateral Spread of Heavy Ions Implanted into Silicon' <i>Rad. Effects</i> , 29 , 189-90 (1976) <i>Comment</i> : dR(Lateral). (10-40 keV) Cu, Cd, Xe, Dy, Kr, W, Pb, Bi -> Si	1976-Gran3

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1980	Gamo, K. Yagita, H. Takai, M. Namba, S. Takigawa, M. 'Ion Implantation of Zn, Se, and Cd in BP Crystals' <i>Rad. Effects, 47, 45-50 (1980)</i> <i>Comment : R, dR. 70 keV Zn, Se, Cd -> BP (crystal)</i>	1980-Gamo
